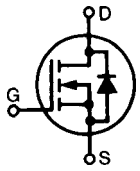
IXYS

MegaMOS™FET

IXTH 14N80

V_{DSS} = 800 V
I_{D25} = 14 A
$R_{DS(on)}$ = 0.70 Ω

N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	800	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	800	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	14	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	56	A
P_D	T_C = 25°C	300	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Max. lead temperature for soldering 1.6 mm (0.063 in) from case for 10 s		300	°C
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

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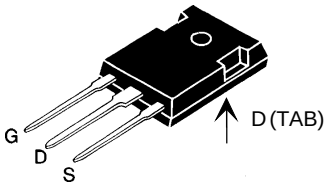


G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard package
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
  - easy to drive and to protect
- Fast switching times

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 3 mA	800			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4.5	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	V_{DS} = 0.8 • V_{DSS} T_J = 25°C V_{GS} = 0 V T_J = 125°C			250 1	µA mA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 I_{D25} Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			0.7	Ω

Applications

- Switch-mode and resonant-mode power supplies
- Motor control
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

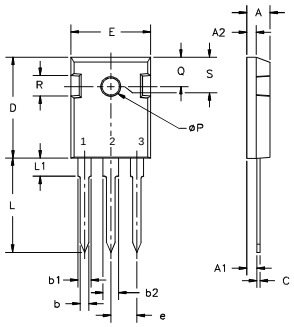
- Easy to mount with 1 screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	min.	typ.	max.	
Characteristic Values					
g_{fs}	V_{DS} = 10 V; I_D = 0.5 • I_{D25}, pulse test	8	14		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4500		pF
C_{oss}			310		pF
C_{rss}			65		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 I_{D25} R_G = 2 Ω, (External)		20	50	ns
t_r			33	50	ns
$t_{d(off)}$			63	100	ns
t_f			32	50	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 I_{D25}		145	170	nC
Q_{gs}			30	45	nC
Q_{gd}			55	80	nC
R_{thJC}				0.42	K/W
R_{thCK}			0.25		K/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	min.	typ.	max.	
Characteristic Values					
I_S	V_{GS} = 0 V			14	A
I_{SM}	Repetitive; pulse width limited by T_{JM}			56	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.5	V
t_{rr}	I_F = I_S, -di/dt = 100 A/µs, V_R = 100 V		800		ns

TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

Figure 1. Output Characteristics at 25°C

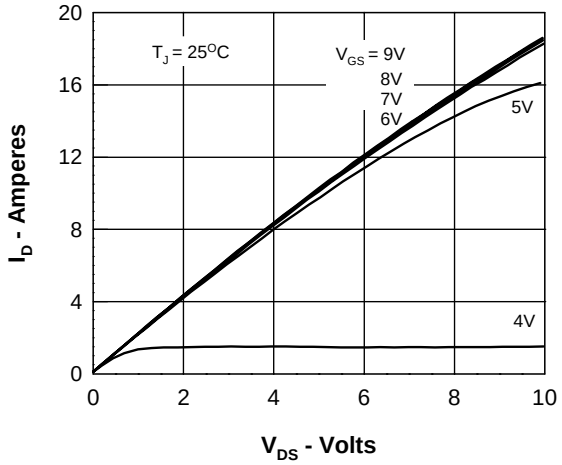


Figure 2. Output Characteristics at 125°C

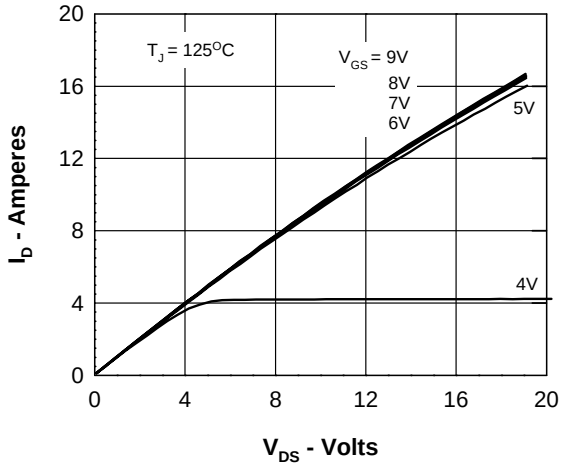


Figure 3. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. I_D

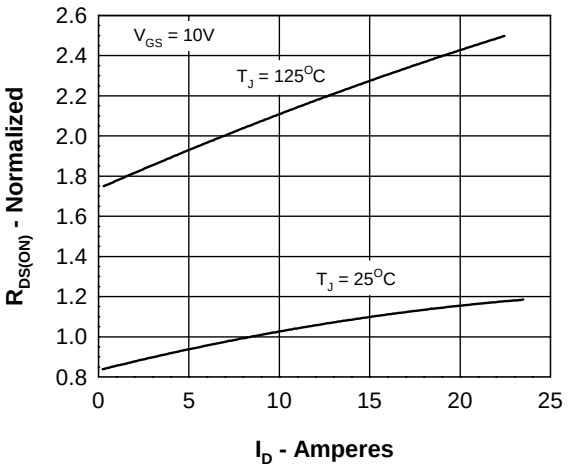


Figure 4. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. T_J

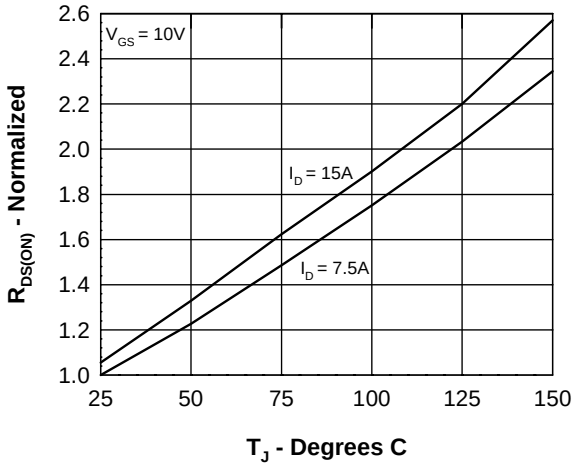


Figure 5. Drain Current vs. Case Temperature

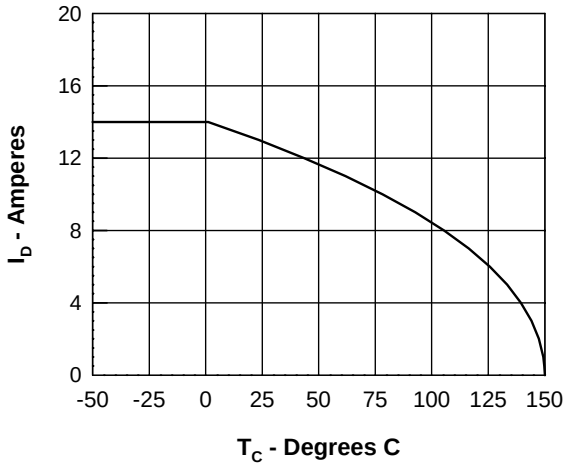


Figure 6. Admittance Curves

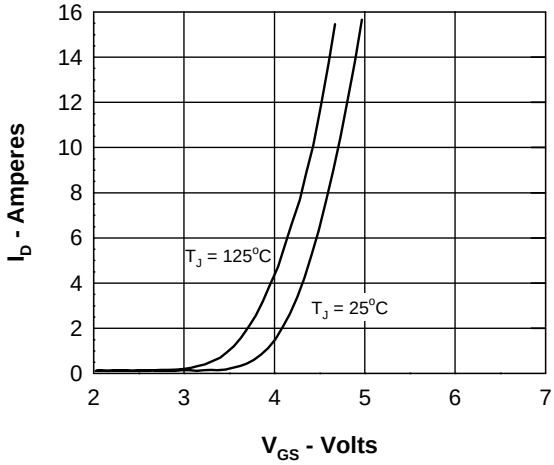


Figure 7. Gate Charge

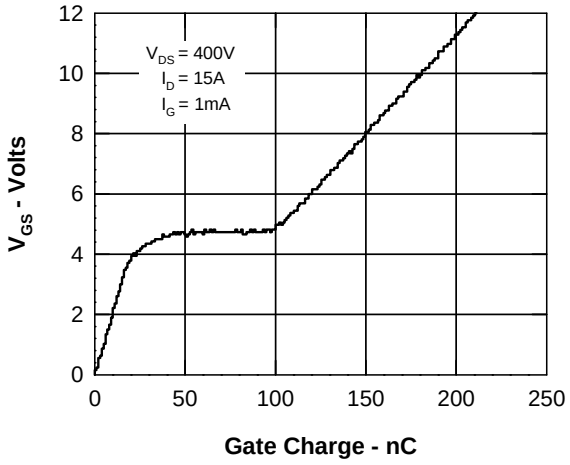


Figure 8. Capacitance Curves

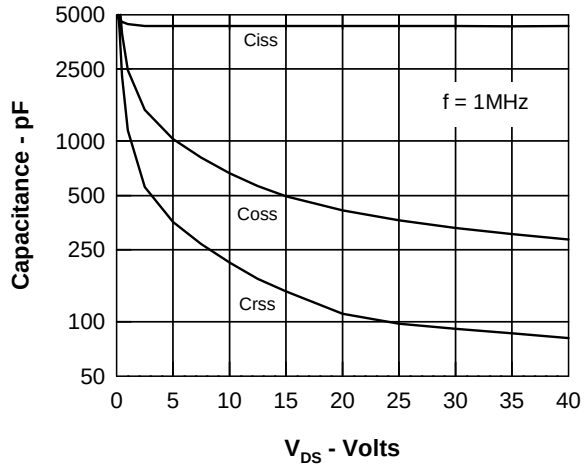


Figure 9. Source Current vs. Source to Drain Voltage

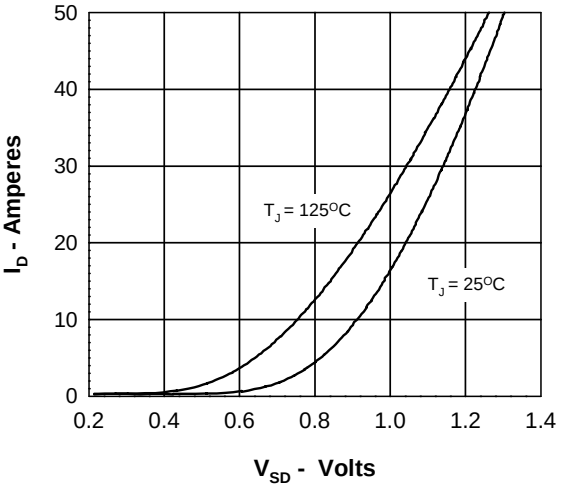


Figure10. Forward Bias Safe Operating Area

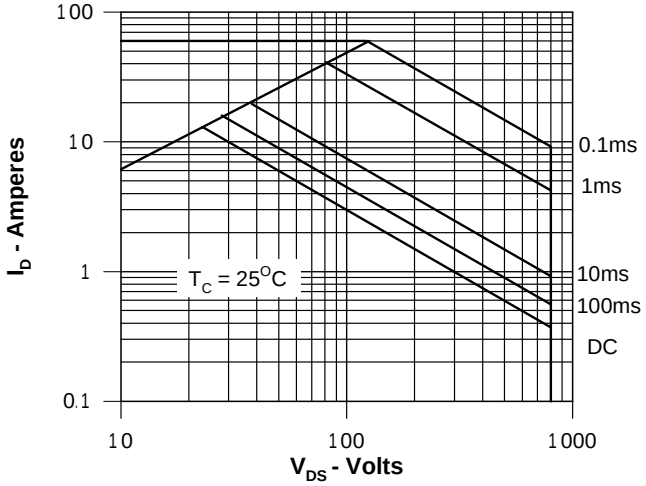


Figure 11. Transient Thermal Resistance